ABSTRACT OF THE DISCLOSURE

[0045] A method for fabricating a semiconductor product first provides an embedded semiconductor product comprising: (1) a logic region having formed therein a logic field effect transistor device; (2) a memory region having formed therein a memory field effect transistor device; and (3) a kerf region having formed therein a kerf field effect transistor device. The method also provides for measuring for the embedded semiconductor product a gate electrode linewidth for each of the logic field effect transistor device, the memory field effect transistor device and the kerf field effect transistor device. The measured gate electrode linewidths may be compared among themselves or to specified target values for purposes photoexposure process control.